

SN54LS630, SN54LS631, SN74LS630, SN74LS631

16-BIT PARALLEL ERROR DETECTION AND CORRECTION CIRCUITS

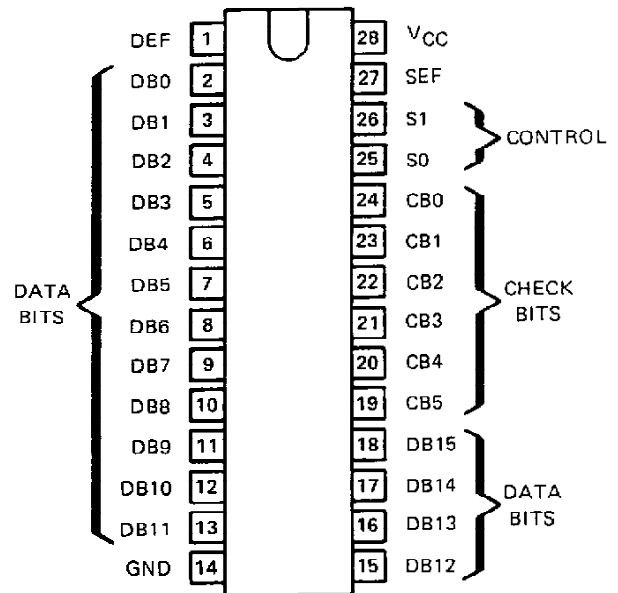
SDLS187

D2550, MARCH 1980

(TIM99630, TIM99631)

- Detects and Corrects Single-Bit Errors
- Detects and Flags Dual-Bit Errors
- Fast Processing Times:
 - Write Cycle: Generates Check Word in 45 ns Typical
 - Read Cycle: Flags Errors in 27 ns Typical
- Power Dissipation 600 mW Typical
- Choice of Output Configurations:
 - 'LS630 . . . 3-State
 - 'LS631 . . . Open-Collector

SN54LS' . . . JD PACKAGE
SN74LS' . . . JD OR N PACKAGE
(TOP VIEW)



description

The 'LS630 and 'LS631 devices are 16-bit parallel error detection and correction circuits (EDACs) in 28-pin, 600-mil packages. They use a modified Hamming code to generate a 6-bit check word from a 16-bit data word. This check word is stored along with the data word during the memory write cycle. During the memory read cycle, the 22-bit words from memory are processed by the EDACs to determine if errors have occurred in memory.

Single-bit errors in the 16-bit data word are flagged and corrected.

Single-bit errors in the 6-bit check word are flagged, and the CPU sends the EDAC through the correction cycle even though the 16-bit word is not in error. The correction cycle will simply pass along the original 16-bit word in this case and produce error syndrome bits to pinpoint the error-generating location.

Dual-bit errors are flagged but not corrected. These dual errors may occur in any two bits of the 22-bit word from memory (two errors in the 16-bit data word, two errors in the 6-bit check word, or one error in each word).

The gross-error condition of all lows or all highs from memory will be detected. Otherwise, errors in three or more bits of the 22-bit word are beyond the capabilities of these devices to detect.

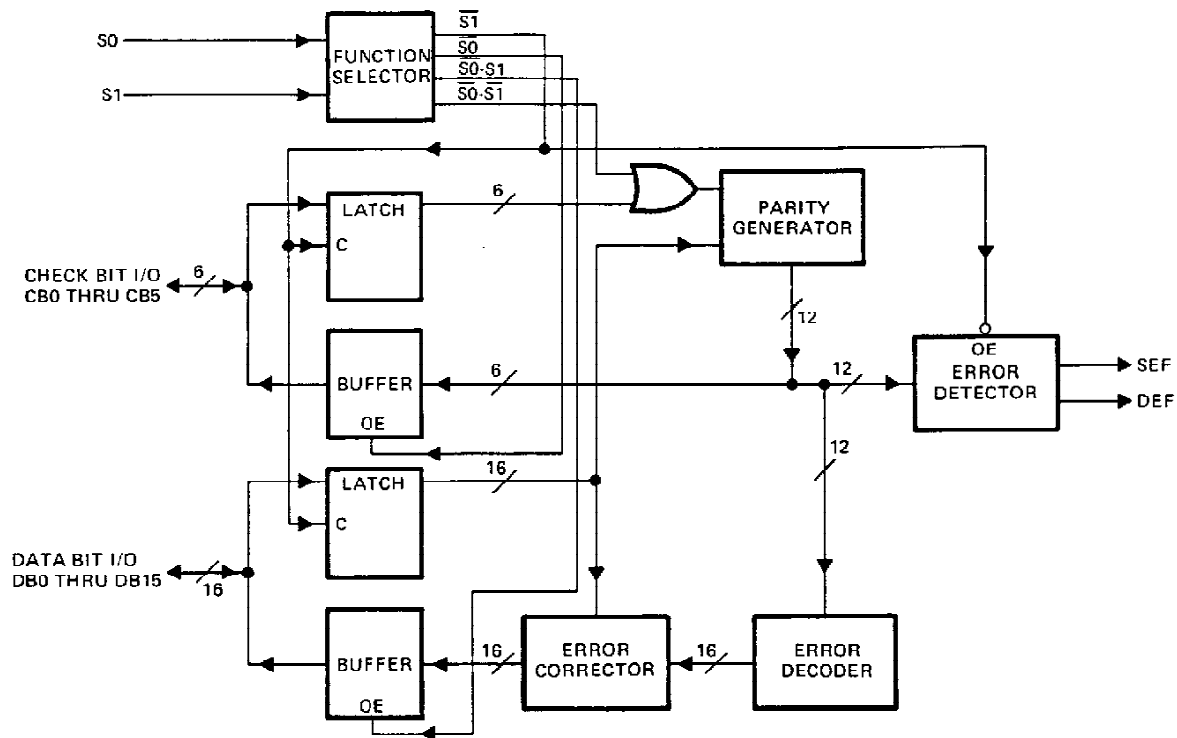
CONTROL FUNCTION TABLE

Memory Cycle	Control		EDAC Function	Data I/O	Check Word I/O	Error Flags	
	S1	S0				SEF	DEF
WRITE	L	L	Generate Check Word	Input Data	Output Check Word	L	L
READ	L	H	Read Data & Check Word	Input Data	Input Check Word	L	L
READ	H	H	Latch & Flag Errors	Latch Data	Latch Check Word	Enabled	
READ	H	L	Correct Data Word & Generate Syndrome Bits	Output Corrected Data	Output Syndrome Bits	Enabled	

SN54LS630, SN54LS631, SN74LS630, SN74LS631

16-BIT PARALLEL ERROR DETECTION AND CORRECTION CIRCUITS

functional block diagram



ERROR FUNCTION TABLE

Total Number of Errors		Error Flags		Data Correction
16-Bit Data	6-Bit Checkword	SEF	DEF	
0	0	L	L	Not Applicable
1	0	H	L	Correction
0	1	H	L	Correction
1	1	H	H	Interrupt
2	0	H	H	Interrupt
0	2	H	H	Interrupt

In order to be able to determine whether the data from the memory is acceptable to use as presented to the bus, the EDAC must be strobed to enable the error flags and the flags will have to be tested for the zero condition.

The first case in the error function table represents the normal, no-error condition. The CPU sees lows on both flags. The next two cases of single-bit errors require data correction. Although the EDAC can discern the single check bit error and ignore it, the error flags are identical to the single error in the 16-bit data word. The CPU will ask for data correction in both cases. An interrupt condition to the CPU results in each of the last three cases, where dual errors occur.

error detection and correction details

During a memory write cycle, six check bits (CB0-CB5) are generated by eight-input parity generators using the data bits as defined below. During a memory read cycle, the 6-bit check word is retrieved along with the actual data.

SN54LS630, SN54LS631, SN74LS630, SN74LS631
16-BIT PARALLEL ERROR DETECTION
AND CORRECTION CIRCUITS

CHECKWORD BIT	16-BIT DATA WORD															
	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
CB0	x	x		x	x				x	x	x				x	
CB1	x		x	x		x	x		x			x			x	
CB2		x	x		x	x		x		x			x			x
CB3	x	x	x				x	x			x	x	x			
CB4				x	x	x	x	x						x	x	x
CB5									x	x	x	x	x	x	x	x

The six check bits are parity bits derived from the matrix of data bits as indicated by "x" for each bit.

Error detection is accomplished as the 6-bit check word and the 16-bit data word from memory are applied to internal parity generators/checkers. If the parity of all six groupings of data and check bits are correct, it is assumed that no error has occurred and both error flags will be low. (It should be noted that the sense of two of the check bits, bits CB0 and CB1, is inverted to ensure that the gross-error condition of all lows and all highs is detected.)

If the parity of one or more of the check groups is incorrect, an error has occurred and the proper error flag or flags will be set high. Any single error in the 16-bit data word will change the sense of exactly three bits of the 6-bit check word. Any single error in the 6-bit check word changes the sense of only that one bit. In either case, the single error flag will be set high while the dual error flag will remain low.

Any two-bit error will change the sense of an even number of check bits. The two-bit error is not correctable since the parity tree can only identify single-bit errors. Both error flags are set high when any two-bit error is detected.

Three or more simultaneous bit errors can fool the EDAC into believing that no error, a correctable error, or an uncorrectable error has occurred and produce erroneous results in all three cases.

Error correction is accomplished by identifying the bad bit and inverting it. Identification of the erroneous bit is achieved by comparing the 16-bit data word and 6-bit check word from memory with the new check word with one (check word error) or three (data word error) inverted bits.

As the corrected word is made available on the data word I/O port, the check word I/O port presents a 6-bit syndrome error code. This syndrome code can be used to identify the bad memory chip.

ERROR SYNDROME TABLE

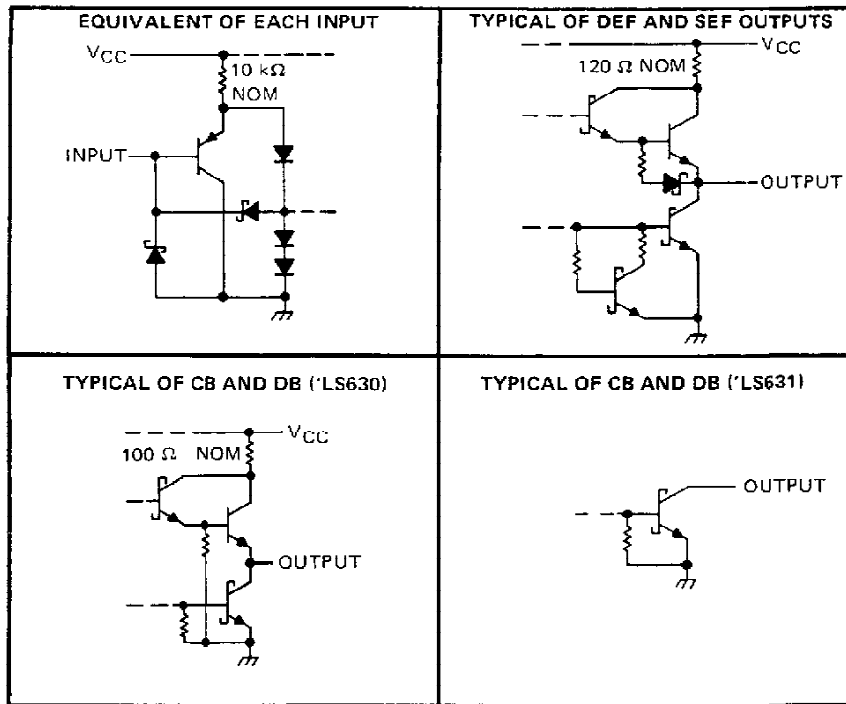
ERROR LOCATION	SYNDROME ERROR CODE					
	CB0	CB1	CB2	CB3	CB4	CB5
DB0	L	L	H	L	H	H
DB1	L	H	L	L	H	H
DB2	H	L	L	L	H	H
DB3	L	L	H	H	L	H
DB4	L	H	L	H	L	H
DB5	H	L	L	H	L	H
DB6	H	L	H	L	L	H
DB7	H	H	L	L	L	H
DB8	L	L	H	H	H	L
DB9	L	H	L	H	H	L
DB10	L	H	H	L	H	L
DB11	H	L	H	L	H	L
DB12	H	H	L	L	H	L
DB13	L	H	H	H	L	L
DB14	H	L	H	H	L	L
DB15	H	H	L	H	L	L
CB0	L	H	H	H	H	H
CB1	H	L	H	H	H	H
CB2	H	H	L	H	H	H
CB3	H	H	H	L	H	H
CB4	H	H	H	H	L	H
CB5	H	H	H	H	H	L
NO ERROR	H	H	H	H	H	H



SN54LS630, SN54LS631, SN74LS630, SN74LS631

16-BIT PARALLEL ERROR DETECTION AND CORRECTION CIRCUITS

schematics of inputs and outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V_{CC} (see Note 1)	7 V
Input voltage: S0 and S1	7 V
CB and DB	5.5 V
Off-state output voltage	5.5 V
Operating free-air temperature range: SN54LS630, SN54LS631	-55°C to 125°C
SN74LS630, SN74LS631	0°C to 70°C
Storage temperature range	-65°C to 150°C

NOTE 1: Voltage Values are with respect to network ground terminal.

recommended operating conditions

		SN54LS630 SN54LS631			SN74LS630 SN74LS631			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
Supply voltage, V_{CC}		4.5	5	5.5	4.75	5	5.25	V
High-level output current, I_{OH}	CB or DB, 'LS630 only			-1			-1	mA
	DEF or SEF			-0.4			-0.4	
High-level output voltage, V_{OH}	CB or DB, 'LS631 only			5.5			5.5	V
Low-level output current, I_{OL}	CB or DB			12			24	mA
	DEF or SEF			4			8	
Setup time, t_{SU}	CB or DB to S1†	30			30			ns
Hold time, t_H	CB or DB after S1†	15			15			ns
Operating free-air temperature, T_A		-55		125	0		70	$^{\circ}\text{C}$

†The upward-pointing arrow indicates a transition from low to high.

SN54LS630, SN54LS631, SN74LS630, SN74LS631 16-BIT PARALLEL ERROR DETECTION AND CORRECTION CIRCUITS

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETERS		TEST CONDITIONS†		SN54LS630		SN74LS630		UNIT	
				MIN	TYP‡	MAX	MIN		TYP‡
V _{IH}	High-level input voltage			2		2		V	
V _{IL}	Low-level input voltage				0.7		0.8	V	
V _{IK}	Input clamp voltage		V _{CC} = MIN, I _I = -18 mA		-1.5		-1.5	V	
V _{OH}	High-level output voltage	CB or DB	V _{CC} = MIN, V _{IH} = 2 V, V _{IL} = V _{IL} min	I _{OH} = MAX	2.4	3.3	2.4	3.2	V
		DEF or SEF		I _{OH} = -400 μA	2.5	3.4	2.7	3.4	
V _{OL}	Low-level output voltage	CB or DB	V _{CC} = MIN, V _{IH} = 2 V, V _{IL} = V _{IL} max	I _{OL} = 12 mA	0.25	0.4	0.25	0.4	V
				I _{OL} = 24 mA			0.35	0.5	
		DEF or SEF		I _{OL} = 4 mA	0.25	0.4	0.25	0.4	
				I _{OL} = 8 mA			0.35	0.5	
I _{OZH}	Off-state output current, high-level voltage applied	CB or DB	V _{CC} = MAX, S ₀ and S ₁ at 2 V	V _O = 2.7 V		20		20	μA
I _{OZL}	Off-state output current, low-level voltage applied	CB or DB	V _{CC} = MAX, S ₀ and S ₁ at 2 V	V _O = 0.4 V		-200		-200	μA
I _I	Input current at maximum input voltage	CB or DB	V _{CC} = MAX, V _I = 5.5 V			0.1		0.1	mA
		S ₀ or S ₁	V _{IH} = 4.5 V, V _I = 7 V			0.1		0.1	
I _{IH}	High-level input current		V _{CC} = MAX, V _I = 2.7 V			20		20	μA
I _{IL}	Low-level input current		V _{CC} = MAX, V _I = 0.4 V			-0.2		-0.2	mA
I _{OS}	Short-circuit output current¶	CB or DB	V _{CC} = MAX		-30	-130	-30	-130	mA
		DEF or SEF			-20	-100	-20	-100	
I _{CC}	Supply current		V _{CC} = MAX, S ₀ and S ₁ at 4.5 V, All CB and DB pins grounded, DEF and SEF open		143	230	143	230	mA

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS†		SN54LS631		SN74LS631		UNIT	
				MIN	TYP‡	MAX	MIN		TYP‡
V _{IH}	High-level input voltage			2		2		V	
V _{IL}	Low-level input voltage				0.7		0.8	V	
V _{IK}	Input clamp voltage		V _{CC} = MIN, I _I = -18 mA		-1.5		-1.5	V	
V _{OH}	High-level output voltage	DEF or SEF	V _{CC} = MIN, V _{IH} = 2 V, V _{IL} = V _{IL} max	I _{OH} = -400 μA	2.5	3.4	2.7	3.4	V
I _{OH}	High-level output current	CB or DB	V _{CC} = MIN, V _{IH} = 2 V, V _{IL} = V _{IL} max	V _{OH} = 5.5 V		100		100	μA
V _{OL}	Low-level output voltage	CB or DB	V _{CC} = MIN, V _{IH} = 2 V, V _{IL} = V _{IL} max	I _{OL} = 12 mA	0.25	0.4	0.25	0.4	V
				I _{OL} = 24 mA			0.35	0.5	
		DEF or SEF		I _{OL} = 4 mA	0.25	0.4	0.25	0.4	
				I _{OL} = 8 mA			0.35	0.5	
I _I	Input current at maximum input voltage	CB or DB	V _{CC} = MAX, V _I = 5.5 V			0.1		0.1	mA
		S ₀ or S ₁	V _{IH} = 4.5 V, V _I = 7 V			0.1		0.1	
I _{IH}	High-level input current		V _{CC} = MAX, V _I = 2.7 V			20		20	μA
I _{IL}	Low-level input current		V _{CC} = MAX, V _I = 0.4 V			-0.2		-0.2	mA
I _{OS}	Short-circuit output current¶	DEF or SEF	V _{CC} = MAX		-20	-100	-20	-100	mA
I _{CC}	Supply current		V _{CC} = MAX, S ₀ and S ₁ at 4.5 V, All CB and DB grounded, SEF and DEF open		113	180	113	180	mA

† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

‡ All typical values are at V_{CC} = 5 V, T_A = 25°C.

¶ Not more than one output should be shorted at a time, and duration of the short circuit should not exceed one second.


**TEXAS
INSTRUMENTS**

POST OFFICE BOX 225012 • DALLAS, TEXAS 75225

SN54LS630, SN54LS631, SN74LS630, SN74LS631
16-BIT PARALLEL ERROR DETECTION
AND CORRECTION CIRCUITS

switching characteristics, $V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$, $C_L = 45\text{ pF}$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	'LS630			UNIT
				MIN	TYP	MAX	
t _{PLH} Propagation delay time, low-to-high-level output [○]	DB	CB	S0 at 0 V, S1 at 0 V, R _L = 667 Ω, See Figure 1	31	45	ns	
t _{PHL} Propagation delay time, high-to-low-level output [○]				45	65		
t _{PLH} Propagation delay time, low-to-high-level output [*]	S1↑	DEF	S0 at 3 V, R _L = 2 kΩ, See Figure 1	27	40	ns	
		SEF		20	30		
t _{PZH} Output enable time to high level [#]	S0↓	CB, DB	S1 at 3 V, R _L = 667 Ω, See Figure 2	24	40	ns	
t _{PZL} Output enable time to low level [#]	S0↓	CB, DB	S1 at 3 V, R _L = 667 Ω, See Figure 1	30	45	ns	
t _{PHZ} Output disable time from high level [▲]	S0↑	CB, DB	S1 at 3 V, R _L = 667 Ω, See Figure 2	43	65	ns	
t _{PLZ} Output disable time from low level [▲]	S0↑	CB, DB	S1 at 3 V, R _L = 667 Ω, See Figure 1	31	45	ns	

switching characteristics, $V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$, $C_L = 45\text{ pF}$, see Figure 1

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	'LS631			UNIT
				MIN	TYP	MAX	
t _{PLH} Propagation delay time, low-to-high level output [○]	DB	CB	S0 at 0 V, S1 at 0V, R _L = 667 Ω	38	55	ns	
t _{PHL} Propagation delay time, high-to-low-level output [○]				45	65		
t _{PLH} Propagation delay time, low-to-high-level output [*]	S1↑	DEF	S0 at 3 V, R _L = 2 kΩ	27	40	ns	
		SEF		20	30		
t _{PHL} Propagation delay time, high-to-low-level output [#]	S0↓	CB, DB	S1 at 3 V, R _L = 667 kΩ	28	45	ns	
t _{PLH} Propagation delay time, low-to-high-level output [▲]	S0↑	CB, DB	S1 at 3 V, R _L = 667 kΩ	33	50	ns	

[○]These parameters describe the time intervals taken to generate the check word during the memory write cycle.

^{*}These parameters describe the time intervals taken to flag errors during the memory read cycle.

[#]These parameters describe the time intervals taken to correct and output the data word and to generate and output the syndrome error code during the memory read cycle.

[▲]These parameters describe the time intervals taken to disable the CB and DB buses in preparation for a new data word during the memory read cycle.

PARAMETER MEASUREMENT INFORMATION

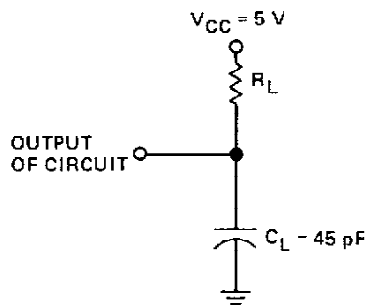


FIGURE 1—OUTPUT LOAD CIRCUIT

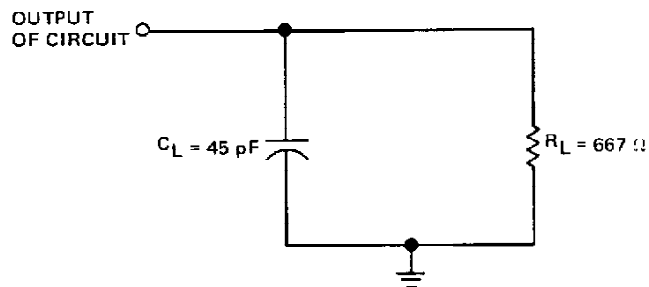


FIGURE 2—OUTPUT LOAD CIRCUIT

TEXAS
INSTRUMENTS

POST OFFICE BOX 225012 • DALLAS, TEXAS 75265

IMPORTANT NOTICE

Texas Instruments (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Certain applications using semiconductor products may involve potential risks of death, personal injury, or severe property or environmental damage ("Critical Applications").

TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS.

Inclusion of TI products in such applications is understood to be fully at the risk of the customer. Use of TI products in such applications requires the written approval of an appropriate TI officer. Questions concerning potential risk applications should be directed to TI through a local SC sales office.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

IMPORTANT NOTICE

Texas Instruments (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Certain applications using semiconductor products may involve potential risks of death, personal injury, or severe property or environmental damage ("Critical Applications").

TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS.

Inclusion of TI products in such applications is understood to be fully at the risk of the customer. Use of TI products in such applications requires the written approval of an appropriate TI officer. Questions concerning potential risk applications should be directed to TI through a local SC sales office.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.